



Average gate power dissipation ($T_j=150$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	22	W
Peak pulse voltage ($T_j=25$; non-repetitive,off-state;FIG.7)	V_{pp}	1	kV

($T_j=25$

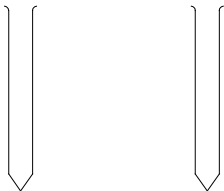
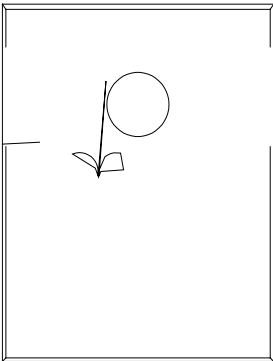
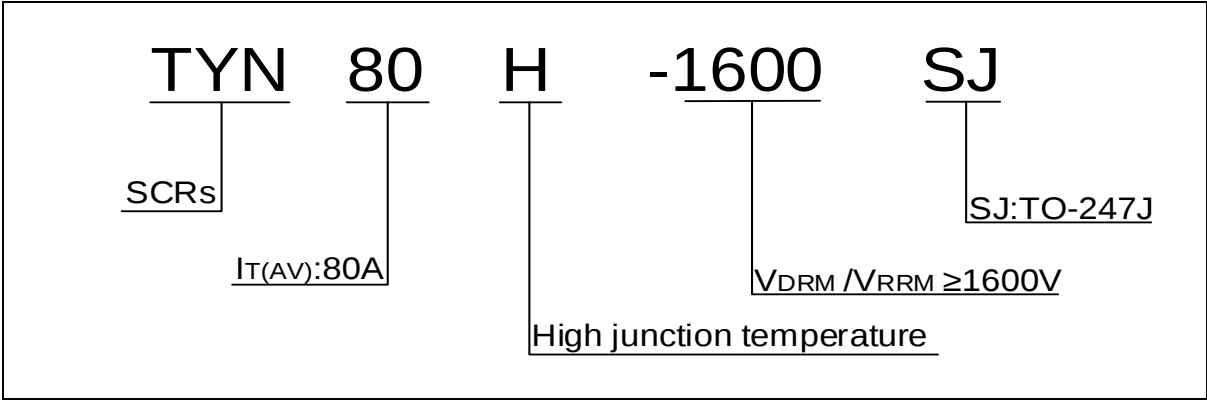
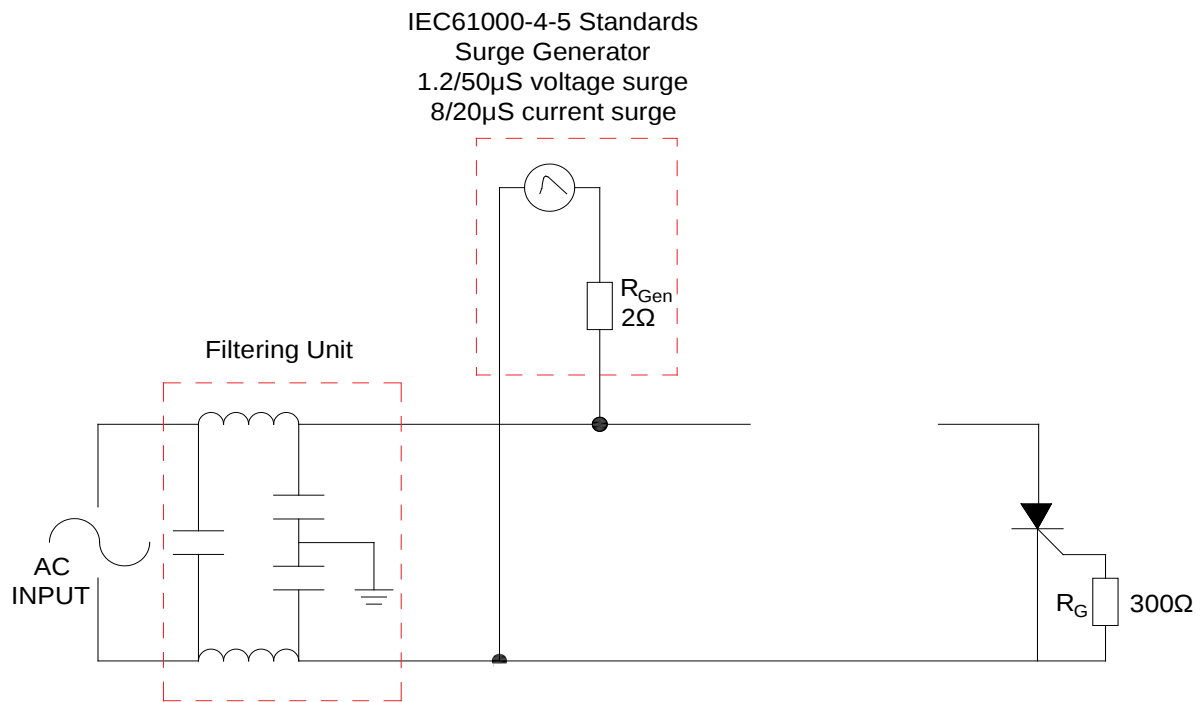
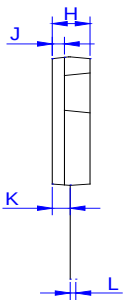
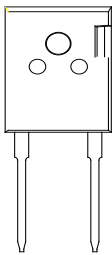


FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.





Order code	Voltage $V_{\text{DRM}}/V_{\text{RRM}}$ (V)	IGT(mA)	
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Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	15.50		16.10	0.610		0.634
B1	3.10		3.50	0.122		0.138
C	19.70		20.30	0.776		0.799
D	2.90		3.30	0.114		0.130
E	1.90		2.30	0.075		0.091
F	1.00		1.40	0.039		0.055
G		5.44			0.214	

H	4.80	5.20	0.189	0.205
J	1.90	2.10	0.075	0.083
K	2.20	2.50	0.087	0.098
L	0.41	0.79	0.016	0.031

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